

Application No.: 10/776,228Docket No.: 2336-241

ABSTRACT

~~Disclosed herein is a~~ A method of manufacturing a nitride semiconductor light emitting device~~[[.]]includes growing a nitride semiconductor crystal film-is grown~~ on a substrate. The nitride semiconductor crystal film has a composition represented as $Al_xIn_yGa_{(1-x-y)}N$ ($0 \leq x \leq 1$, $0 \leq y \leq 1$, $0 \leq x+y \leq 1$). After that, in order to remove an oxide film naturally formed on the nitride semiconductor crystal film, a surface treatment process is performed on the nitride semiconductor crystal film by making use of hydrogen gas or mixed gases containing hydrogen. Subsequently, on the nitride semiconductor crystal film, ~~there are successively formed~~ a first conductive nitride semiconductor layer, an active layer, and a second conductive nitride semiconductor layer are successively formed.